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# ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3

# EcoSPARK<sup>®</sup> 300mJ, 400V, N-Channel Ignition IGBT

## **General Description**

The ISL9V3040D3S, ISL9V3040S3S, ISL9V3040P3, and ISL9V3040S3 are the next generation ignition IGBTs that offer outstanding SCIS capability in the space saving D-Pak (TO-252), as well as the industry standard D²-Pak (TO-263), and TO-262 and TO-220 plastic packages. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

**EcoSPARK¤** devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

Formerly Developmental Type 49362

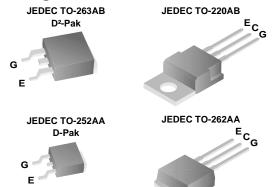
## **Applications**

- · Automotive Ignition Coil Driver Circuits
- · Coil- On Plug Applications

## **Features**

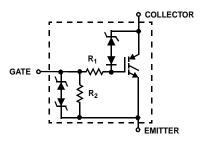
- · Space saving D-Pak package availability
- SCIS Energy = 300mJ at T<sub>J</sub> = 25°C
- · Logic Level Gate Drive

## **Package**



COLLECTOR (FLANGE)

## **Symbol**



## **Device Maximum Ratings** T<sub>A</sub> = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
BV <sub>CER</sub>	Collector to Emitter Breakdown Voltage (I <sub>C</sub> = 1 mA)	430	V
BV <sub>ECS</sub>	Emitter to Collector Voltage - Reverse Battery Condition (I <sub>C</sub> = 10 mA)	24	V
E <sub>SCIS25</sub>	At Starting T <sub>J</sub> = 25°C, I <sub>SCIS</sub> = 14.2A, L = 3.0 mHy	300	mJ
E <sub>SCIS150</sub>	At Starting T <sub>J</sub> = 150°C, I <sub>SCIS</sub> = 10.6A, L = 3.0 mHy	170	mJ
I <sub>C25</sub>	Collector Current Continuous, At T <sub>C</sub> = 25°C, See Fig 9	21	Α
I <sub>C110</sub>	Collector Current Continuous, At T <sub>C</sub> = 110°C, See Fig 9	17	Α
$V_{GEM}$	Gate to Emitter Voltage Continuous	±10	V
P <sub>D</sub>	Power Dissipation Total T <sub>C</sub> = 25°C	150	W
	Power Dissipation Derating T <sub>C</sub> > 25°C	1.0	W/°C
TJ	Operating Junction Temperature Range	-40 to 175	°C
T <sub>STG</sub>	Storage Junction Temperature Range	-40 to 175	°C
TL	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	°C
T <sub>pkg</sub>	Max Lead Temp for Soldering (Package Body for 10s)	260	°C
ESD	Electrostatic Discharge Voltage at 100pF, 1500Ω	4	kV

Package	Mark	ing and Ordering	j Inf	ormation						
Device M	arking	Device	P	Package	Reel Size	Тар	e Width	Qua	Quantity	
V304	0D	ISL9V3040D3ST	TO	O-252AA	330mm	16mm		2	2500	
V304	0S	ISL9V3040S3ST	TO-263AB		330mm	24mm		8	800	
V304	0P	ISL9V3040P3	TO-220AA		Tube	N/A		50		
V304	0S	ISL9V3040S3	T	TO-262AA Tube		N/A		50		
V304	0D	ISL9V3040D3S	TO-252AA		Tube	N/A		75		
V3040S ISL9V3040S3S		TO-263AB		Tube	N/A		50			
Electrica	al Cha	racteristics T <sub>A</sub> = 25	°C un	less otherwise	noted	·L				
Symbol		Parameter		1	nditions	Min	Тур	Max	Units	
off State	Charact	teristics					•			
BV <sub>CER</sub>	Collecto	r to Emitter Breakdown Vol	$I_C$ = 2mA, $V_{GE}$ = 0, $R_G$ = 1KΩ, See Fig. 15 $T_J$ = -40 to 150°C		370	400	430	V		
BV <sub>CES</sub>	Collecto	r to Emitter Breakdown Vol	tage	I <sub>C</sub> = 10mA, V <sub>GE</sub> = 0, R <sub>G</sub> = 0, See Fig. 15 T <sub>J</sub> = -40 to 150°C		390	420	450	V	
BV <sub>ECS</sub>	Emitter t	o Collector Breakdown Vol	tage	I <sub>C</sub> = -75mA, V T <sub>C</sub> = 25°C		30	-	-	V	
BV <sub>GES</sub>	Gate to	Emitter Breakdown Voltage	;	I <sub>GES</sub> = ± 2mA		±12	±14	-	V	
I <sub>CER</sub>	Collector to Emitter Leakage Current		V <sub>CER</sub> = 250V,		-	-	25	μΑ		
				$R_G = 1K\Omega$ , See Fig. 11	T <sub>C</sub> = 150°C	-	-	1	mA	
I <sub>ECS</sub>	Emitter t	o Collector Leakage Curre	nt	V <sub>EC</sub> = 24V, Se	e T <sub>C</sub> = 25°C	-	-	1	mA	
				Fig. 11	T <sub>C</sub> = 150°C	-	-	40	mA	
R <sub>1</sub>	Series G	Sate Resistance			-	70	-	Ω		
R <sub>2</sub>	Gate to	Emitter Resistance			10K	-	26K	Ω		
n State (	Charact	eristics								
V <sub>CE(SAT)</sub>	Collecto	r to Emitter Saturation Volt	age	I <sub>C</sub> = 6A, V <sub>GE</sub> = 4V	T <sub>C</sub> = 25°C, See Fig. 3	-	1.25	1.60	V	
V <sub>CE(SAT)</sub>	Collecto	r to Emitter Saturation Voltage		I <sub>C</sub> = 10A, V <sub>GE</sub> = 4.5V	T <sub>C</sub> = 150°C, See Fig. 4	-	1.58	1.80	V	
V <sub>CE(SAT)</sub>	Collecto	or to Emitter Saturation Voltage		$I_C = 15A,$ $V_{GE} = 4.5V$	T <sub>C</sub> = 150°C	-	1.90	2.20	V	
ynamic (	Charact	teristics								
$Q_{G(ON)}$	Gate Ch	arge		I <sub>C</sub> = 10A, V <sub>CE</sub> = 12V, V <sub>GE</sub> = 5V, See Fig. 14		-	17	-	nC	
V <sub>GE(TH)</sub>	Gate to	Emitter Threshold Voltage		$I_C = 1.0 \text{mA},$	T <sub>C</sub> = 25°C	1.3	-	2.2	V	
				V <sub>CE</sub> = V <sub>GE,</sub> See Fig. 10	T <sub>C</sub> = 150°C	0.75	-	1.8	V	
$V_{GEP}$	Gate to	Emitter Plateau Voltage		$I_C$ = 10A, $V_{CE}$	= 12V	-	3.0	-	V	
witching	Chara	cteristics								
t <sub>d(ON)R</sub>	Current	Turn-On Delay Time-Resis	tive	V <sub>CE</sub> = 14V, R <sub>L</sub>		-	0.7	4	μs	
t <sub>rR</sub>		Rise Time-Resistive		$V_{GE}$ = 5V, $R_{G}$ $T_{J}$ = 25°C, Se	-	2.1	7	μs		
t <sub>d(OFF)L</sub>	Current	Turn-Off Delay Time-Induc	tive	V <sub>CE</sub> = 300V, L = 500μHy,		-	4.8	15	μs	
t <sub>fL</sub>		Fall Time-Inductive		$V_{GE}$ = 5V, $R_{G}$ $T_{J}$ = 25°C, Se	-	2.8	15	μs		
SCIS	Self Cla	mped Inductive Switching		$T_J$ = 25°C, L = $R_G$ = 1KΩ, $V_0$ Fig. 1 & 2	-	-	300	mJ		
hermal C	Charact	eristics	_							
$R_{\theta JC}$	Thermal	Resistance Junction-Case	е	All packages			-	1.0	°C/V	

## **Typical Performance Curves**

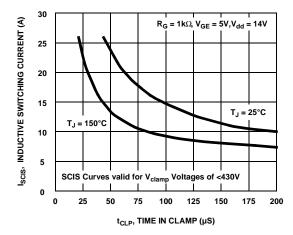


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

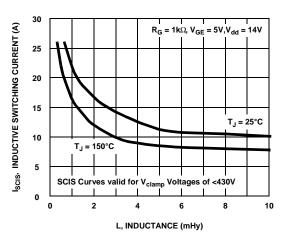


Figure 2. Self Clamped Inductive Switching Current vs Inductance

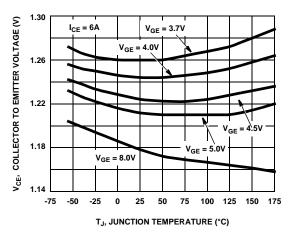


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

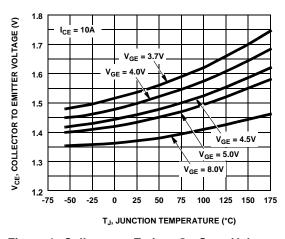


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

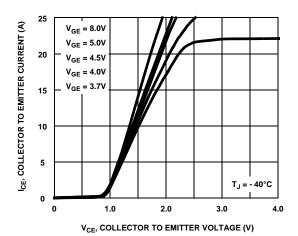


Figure 5. Collector to Emitter On-State Voltage vs Collector Current

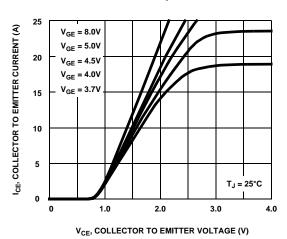
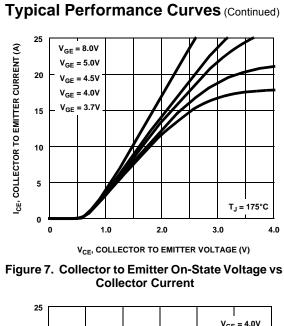


Figure 6. Collector to Emitter On-State Voltage vs Collector Current



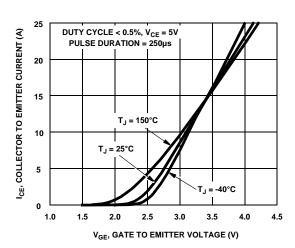
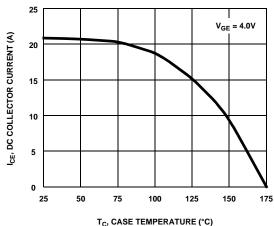


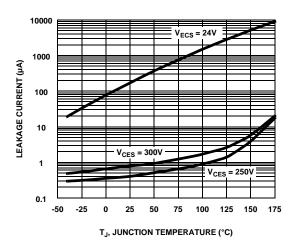
Figure 8. Transfer Characteristics



2.2 V<sub>CE</sub> = V<sub>GE</sub> I<sub>CE</sub> = 1mA 2.0 THRESHOLD VOLTAGE (V) 1.8 1.6 1.4 1.2 -50 -25 50 100 125 150 175 T<sub>J</sub> JUNCTION TEMPERATURE (°C)

Figure 9. DC Collector Current vs Case Temperature

Figure 10. Threshold Voltage vs Junction Temperature



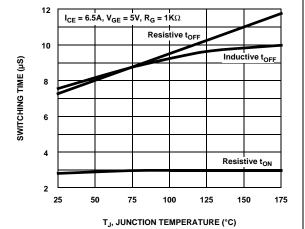


Figure 11. Leakage Current vs Junction Temperature

Figure 12. Switching Time vs Junction Temperature

## **Typical Performance Curves** (Continued) FREQUENCY = 1 MHz 1200 C, CAPACITANCE (pF) 800 C<sub>RES</sub> 400 $c_{\text{oes}}$ 0 15 10 V<sub>CE</sub>, COLLECTOR TO EMITTER VOLTAGE (V) Figure 13. Capacitance vs Collector to Emitter Voltage 430 I<sub>CER</sub> = 10mA 425

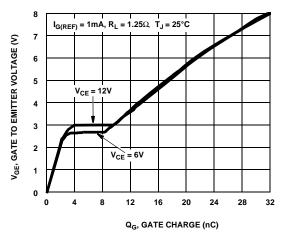


Figure 14. Gate Charge

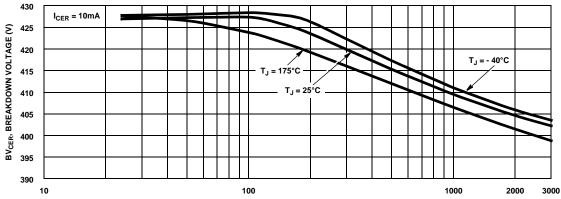


Figure 15. Breakdown Voltage vs Series Gate Resistance

 $R_G$ , SERIES GATE RESISTANCE ( $\Omega$ )

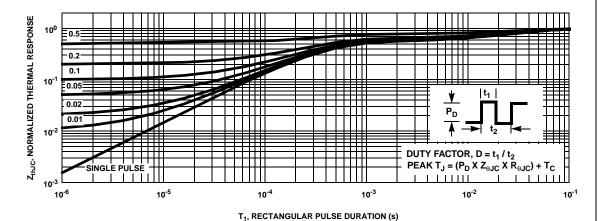
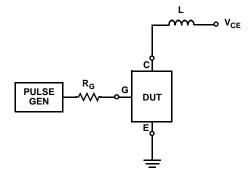


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

## **Test Circuit and Waveforms**



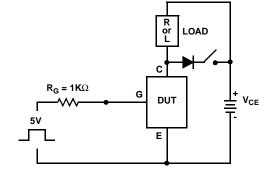
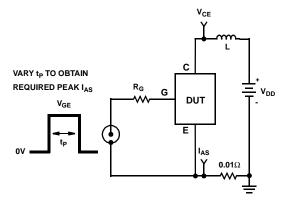


Figure 17. Inductive Switching Test Circuit

Figure 18.  $t_{ON}$  and  $t_{OFF}$  Switching Test Circuit

BV<sub>CES</sub>



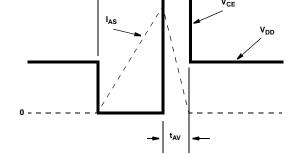


Figure 19. Energy Test Circuit

Figure 20. Energy Waveforms

#### SPICE Thermal Model REV 7 March 2002 JUNCTION ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3 CTHERM1 th 6 2.1e -3 CTHERM2 6 5 1.4e -1 CTHERM3 5 4 7.3e -3 CTHERM4 4 3 2.1e -1 RTHERM1 CTHERM1 CTHERM5 3 2 1.1e -1 CTHERM6 2 tl 6.2e +6 RTHERM1 th 6 1.2e -1 6 RTHERM2 6 5 1.9e -1 RTHERM3 5 4 2.2e -1 RTHERM4 4 3 6.0e -2 RTHERM2 CTHERM2 RTHERM5 3 2 5.8e -2 RTHERM6 2 tl 1.6e -3 SABER Thermal Model 5 SABER thermal model ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3 RTHERM3 CTHERM3 template thermal\_model th tl thermal\_c th, tl 4 ctherm.ctherm1 th 6 = 2.1e -3 ctherm.ctherm2 6 5 = 1.4e -1 ctherm.ctherm3 5 4 = 7.3e -3 ctherm.ctherm4 4 3 = 2.2e -1 RTHERM4 CTHERM4 ctherm.ctherm5 3 2 =1.1e -1 ctherm.ctherm6 2 tl = 6.2e +6 rtherm.rtherm1 th 6 = 1.2e -1 3 rtherm.rtherm2 6 5 = 1.9e - 1rtherm.rtherm3 5 4 = 2.2e -1 rtherm.rtherm4 4 3 = 6.0e -2 RTHERM5 CTHERM5 rtherm.rtherm5 3 2 = 5.8e -2 rtherm.rtherm6 2 tl = 1.6e -3 2 RTHERM6 CTHERM6

CASE

tl





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Definition of Terms						
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Rev. 166

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